

GSDB320B Series

Surface Mount Schottky Barrier Rectifiers

Product Description

Reverse Voltage 20V To 200V Forward Current 3.0A

Features

- Low profile package
- Ideal for automated placement
- Guard ring for over voltage protection
- Low forward voltage drop
- Lead(Pb)-Free

Mechanical Data

- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Terminals: Lead Free Plating (Tin Finish). Solder able per MIL-STD-202, Method 208
- Polarity: Cathode Band
- Weight: 0.095grams (approximate)

Packages



SMB (DO-214AA)

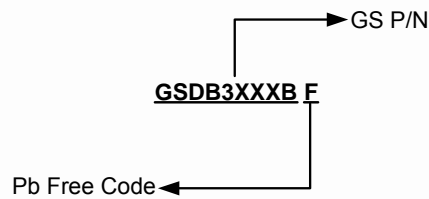
Marking Information

| P/N | Package | Part Marking | Quantity |
|------------|----------------|-------------------|----------|
| GSDB320BF | SMB (DO-214AA) | WTYYWW B320B. | 3000 PCS |
| GSDB330BF | SMB (DO-214AA) | WTYYWW B330B. | |
| GSDB340BF | SMB (DO-214AA) | WTYYWW B340B. | |
| GSDB350BF | SMB (DO-214AA) | WTYYWW B350B. | |
| GSDB360BF | SMB (DO-214AA) | WTYYWW B360B. | |
| GSDB380BF | SMB (DO-214AA) | WTYYWW B380B. | |
| GSDB3100BF | SMB (DO-214AA) | WTYYWW B3100B. | |
| GSDB3150BF | SMB (DO-214AA) | WTYYWW B3150B. | |
| GSDB3200BF | SMB (DO-214AA) | WTYYWW B3200B. | |

※ "WT" GS Code & "YYWW" Date Code

※ "B3XXXB" GS P/N & "." Halogen Free

Ordering Information



Electrical Characteristics

(T_A = 25°C unless otherwise noted)

| Symbol | Conditions | B320B | B330B | B340B | B350B | B360B | Unit |
|------------------|--|------------------------|--------|--------|--------|-------|------|
| V _{RRM} | Maximum Repetitive Peak Reverse Voltage | 20 | 30 | 40 | 50 | 60 | V |
| V _{RMS} | Maximum RMS Voltage | 14 | 21 | 28 | 35 | 42 | V |
| V _{DC} | Maximum DC Blocking Voltage | 20 | 30 | 40 | 50 | 60 | V |
| V _F | Maximum Instantaneous I _F =3A | 0.5 | | 0.62 | | | V |
| I _R | Maximum DC Reverse Current At Rated DC Blocking Voltage | T _J = 25°C | 0.5 | | | | mA |
| | | T _J = 100°C | 10 | | | | |
| C _J | Typical Junction Capacitance (Note 1) | 180 | | | 150 | | pF |
| Symbol | Conditions | B380B | B3100B | B3150B | B3200B | Unit | |
| V _{RRM} | Maximum Repetitive Peak Reverse Voltage | 80 | 100 | 150 | 200 | V | |
| V _{RMS} | Maximum RMS Voltage | 56 | 70 | 105 | 140 | V | |
| V _{DC} | Maximum DC Blocking Voltage | 80 | 100 | 150 | 200 | V | |
| V _F | Maximum Instantaneous I _F =3A | 0.8 | | 0.83 | 0.85 | V | |
| I _R | Maximum DC Reverse Current At Rated DC Blocking Voltage | T _J = 25°C | 0.2 | | | mA | |
| | | T _J = 100°C | 5 | | | | |
| C _J | Typical Junction Capacitance (Note 1) | 110 | | 100 | 80 | pF | |
| I _F | Maximum Average Forward Rectified Current | 3 | | | | A | |
| I _{FSM} | Peak Forward Surge Current, 8.3ms Single Half Sine-Wave Superimposed on Rated Load | 80 | | | | A | |
| R _{θJA} | Thermal Resistance Junction to Ambient | 70 | | | | °C/W | |
| R _{θJC} | Thermal Resistance Junction to Case | 30 | | | | °C/W | |
| T _J | Operating Temperature Range | -55 to +125 | | | | °C | |
| T _{STG} | Storage Temperature Range | -55 to +150 | | | | °C | |

Notes: 1. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.

Typical Characteristics

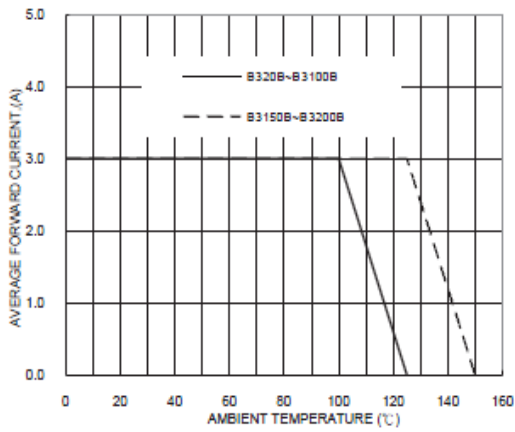


FIG. 1-TYPICAL FORWARD CURRENT DERATING CURVE

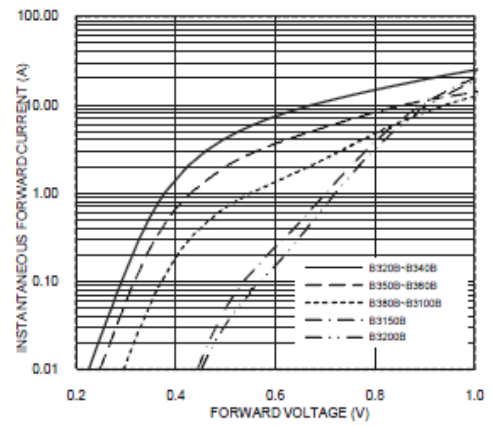


FIG. 2-TYPICAL FORWARD CHARACTERISTICS

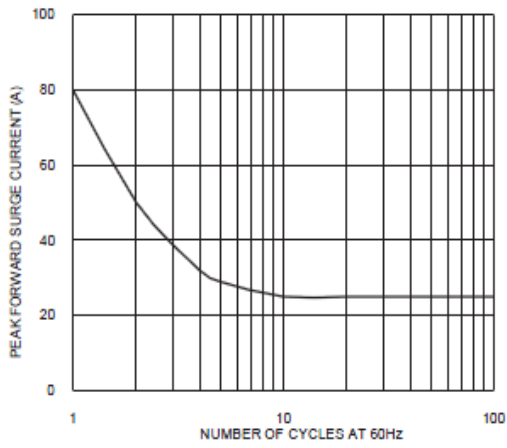


FIG. 3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

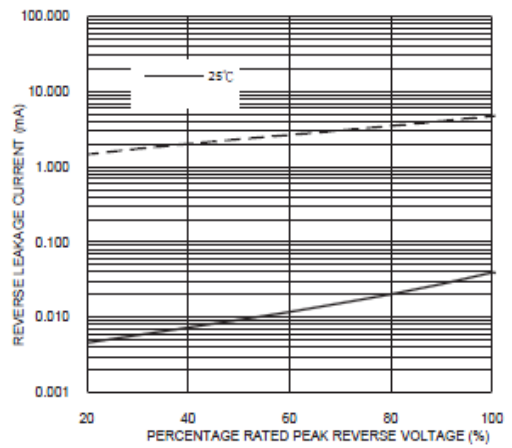


FIG. 4-TYPICAL REVERSE CHARACTERISTICS

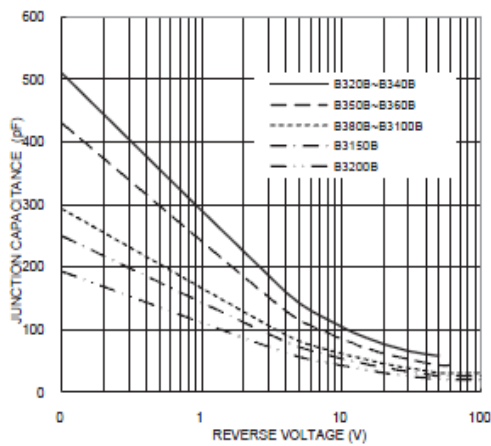
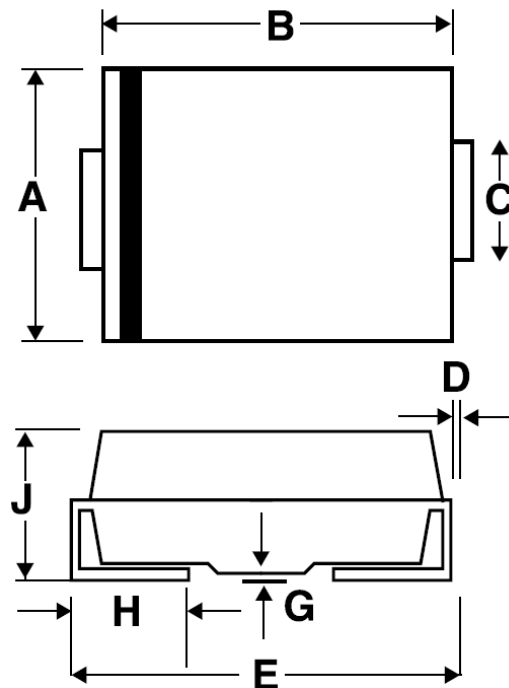


FIG. 5-TYPICAL JUNCTION CAPACITANCE

Package Dimension

SMB (DO-214AA)





| Dimensions | | | | |
|------------|-------------|------|--------|-------|
| Symbol | Millimeters | | Inches | |
| | Min | Max | Min | Max |
| A | 3.30 | 3.94 | 0.129 | 0.155 |
| B | 4.06 | 4.57 | 0.159 | 0.179 |
| C | 1.95 | 2.20 | 0.076 | 0.086 |
| D | 0.15 | 0.31 | 0.005 | 0.012 |
| E | 5.21 | 5.59 | 0.205 | 0.220 |
| G | 0.10 | 0.20 | 0.003 | 0.007 |
| H | 0.76 | 1.52 | 0.029 | 0.059 |
| J | 2.13 | 2.44 | 0.083 | 0.096 |

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